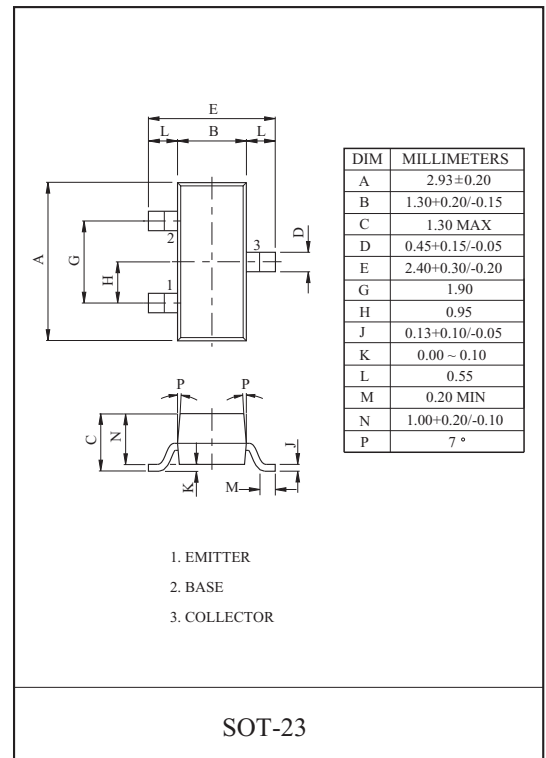


GENERAL PURPOSE HIGH DARLINGTON TRANSISTOR.

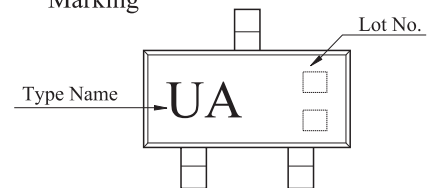
MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	10	V
Collector Current	I _C	400	mA
Collector Power Dissipation	P _C *	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ 150	°C

* : Package Mounted On 99.5% Alumina 10 × 8 × 0.6mm.



Marking



ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V _{(BR)CBO}	I _C =0.1mA	40	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA	30	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-1.0mA	10	-	-	V
Collector Cut-off Current	I _{CBO}	V _{CB} =40V	-	-	1	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} =10V	-	-	1	μA
DC Current Gain	h _{FE}	I _C =100mA, V _{CE} =2V	30K	-	-	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100mA, I _B =1mA	-	-	1	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA	-	1.5	2	V
Current Gain Bandwidth Product	f _T	I _C =100mA, f=100MHz, V _{CE} =2V	-	220	-	MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz	-	5	-	pF

MMBTA517

